ABSTRACT

COMPOSITION FOR PRODUCING A SACRIFICE LAYER AND A PROCESS FOR PRODUCING THE COMPOSITION, AND A SEMICONDUCTOR DEVICE HAVING AIR GAP PRODUCED USING THE COMPOSITION AND A PROCESS FOR A SEMICONDUCTOR DEVICE USING THE COMPOSITION

[Problem]

To provide such a composition for producing a sacrifice layer as has excellent properties in both heat resistance and storage stability, and also to provide a process for producing a semiconductor device using the composition.

[Solution]

Disclosed is a composition for producing a sacrifice layer. The composition comprises a solvent and a polymer having a repeating unit containing a nitrogen atom with a lone pair, and contains particular transition metals only in a very low content. Also disclosed is a process using the composition as a sacrificial material for producing a semiconductor device comprising a porous material.

[Figure 1.]